

## 2N6517

# High Voltage Transistor • Collector-Emitter Voltage: V<sub>CEO</sub>=350V • Collector Dissipation: P<sub>C</sub> (max)=625mW • Complement to 2N6520



## **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	350	V
V <sub>CEO</sub>	Collector-Emitter Voltage	350	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	500	mA
P <sub>C</sub>	Collector Dissipation	625	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

Refer to 2N6515 for graphs

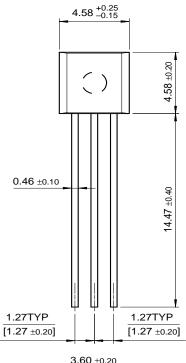
## **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

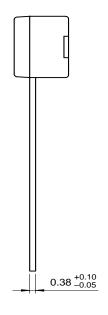
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	* Collector-Emitter Breakdown Voltage	ctor-Emitter Breakdown Voltage I <sub>C</sub> =1mA, I <sub>B</sub> =0 350				V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>E</sub> =0	350			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =250V, I <sub>E</sub> =0			50	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =5V, $I_{C}$ =0			50	nA
h <sub>FE</sub>	* DC Current Gain	I <sub>C</sub> =1mA, V <sub>CE</sub> =10V I <sub>C</sub> =10mA, V <sub>CE</sub> =10V I <sub>C</sub> =30mA, V <sub>CE</sub> =10V I <sub>C</sub> =50mA, V <sub>CE</sub> =10V I <sub>C</sub> =100mA, V <sub>CE</sub> =10V	20 30 30 20 15		200 200	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_{C}$ =10mA, $I_{B}$ =1mA $I_{C}$ =20mA, $I_{B}$ =2mA $I_{C}$ =30mA, $I_{B}$ =3mA $I_{C}$ =50mA, $I_{B}$ =5mA			0.3 0.35 0.5 1	V V V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA I <sub>C</sub> =20mA, I <sub>B</sub> =2mA I <sub>C</sub> =30mA, I <sub>B</sub> =3mA			0.75 0.85 0.9	V V V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =20V, I <sub>E</sub> =0, f=1MHz			6	pF
f <sub>T</sub>	* Current Gain Bandwidth Product	I <sub>C</sub> =10mA, V <sub>CE</sub> =20V, f=20MHz	40		200	MHz
V <sub>BE</sub> (on)	Base Emitter On Voltage	I <sub>C</sub> =100mA, V <sub>CE</sub> =10V			2	V

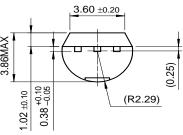
<sup>\*</sup> Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

# **Package Demensions**

TO-92







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